# **BL** Galaxy Electrical

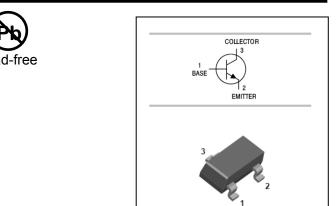
# NPN Silicon Epitaxial Planar Transistor

#### **KTC4075**

**SOT-23** 

#### **FEATURES**

- High and excellent DC current gain.
- Complementary to KTA2014.
- Small package.



#### **APPLICATIONS**

- General purpose application.
- Switching application.

#### **ORDERING INFORMATION**

Type No.	Marking	Package Code	
KTC4075	LO/LY/LGR/LBL	SOT-23	

## MAXIMUM RATING @ Ta=25 °C unless otherwise specified

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current -Continuous	150	mA
I <sub>B</sub>	Base Current	30	mA
Pc	Collector Power Dissipation	100	mW
$T_{j},T_{stg}$	Junction and Storage Temperature	-55~150	$^{\circ}$

Document number: BL/SSSTC112

Rev.A

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## **KTC4075**

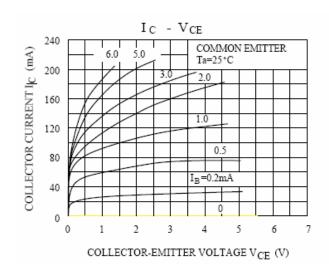
#### ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

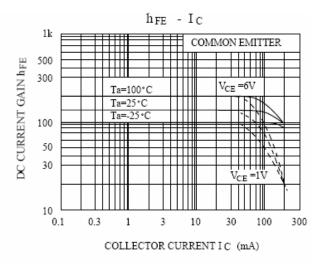
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100μA,I <sub>E</sub> =0	60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA,I <sub>B</sub> =0	50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100μA,I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =60V,I <sub>E</sub> =0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =5V,I <sub>C</sub> =0			0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =6V,I <sub>C</sub> =2mA	70		700	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA		0.1	0.25	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> = 1mA	80			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V,I <sub>E</sub> =0,f=1MHz		2.0	3.5	pF

#### CLASSIFICATION OF hFE

Rank	0	Y	GR	BL
Range	70-140	120-240	200-400	350-700

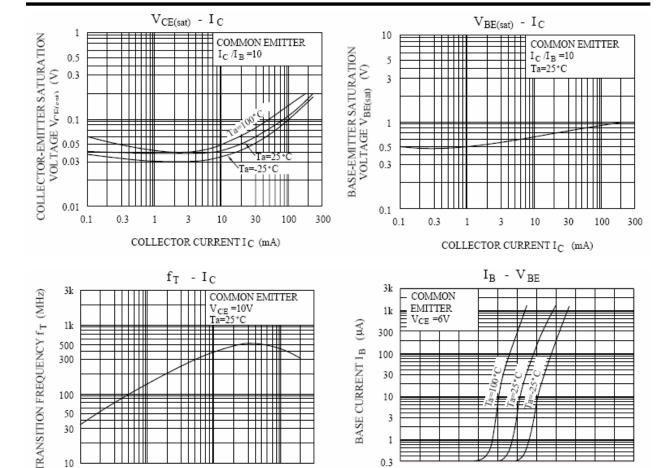
# TYPICAL CHARACTERISTICS @ Ta=25 $^{\circ}$ C unless otherwise specified





# NPN Silicon Epitaxial Planar Transistor

#### **KTC4075**



0.3

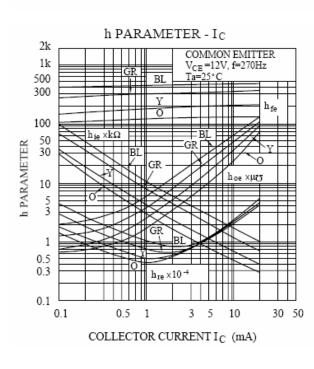
0.2

0.4

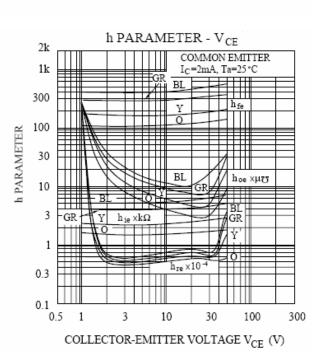
0.6

BASE-EMITTER VOLTAGE V<sub>BE</sub> (V)

1.0



COLLECTOR CURRENT IC (mA)



10

0.1

0.3

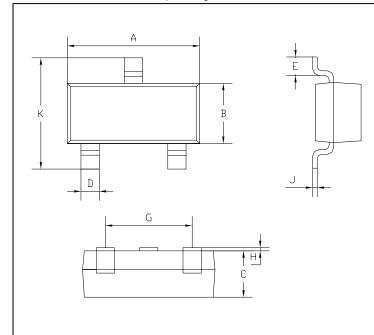
# NPN Silicon Epitaxial Planar Transistor

**KTC4075** 

#### PACKAGE OUTLINE

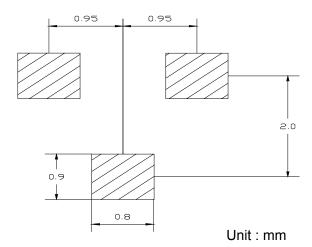
Plastic surface mounted package

SOT-23



SOT-23		
Dim	Min	Max
Α	2.85	2.95
В	1.25	1.35
С	1.0Typical	
D	0.37	0.43
E	0.35	0.48
G	1.85	1.95
Н	0.02	0.1
J	0.1Typical	
K	2.35	2.45
All Dimensions in mm		

#### **SOLDERING FOOTPRINT**



#### PACKAGE INFORMATION

Device	Package	Shipping
KTC4075	SOT-23	3000/Tape&Reel

# www.s-manuals.com